

Silicon NPN Power Transistors

2SC2774

DESCRIPTION

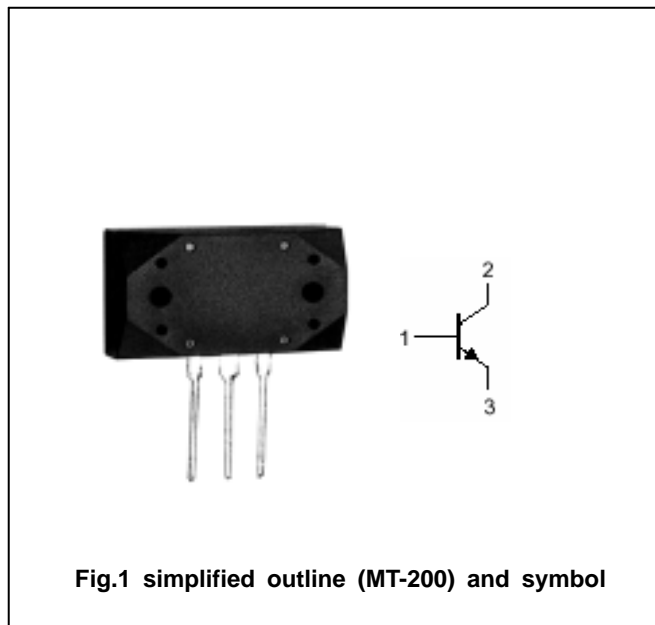
- With MT-200 package
- High power dissipation
- High current capability

APPLICATIONS

- For audio power amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	200	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		17	A
I _B	Base current		5	A
P _C	Collector power dissipation	T _C =25	200	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =4V	50		140	
C _{ob}	Output capacitance	I _E =0 ; V _{CB} =10V;f=1MHz		300		pF
f _T	Transition frequency	I _C =2A ; V _{CE} =12V		20		MHz

◆ h_{FE} classifications

O	Y
50-100	70-140

PACKAGE OUTLINE

